

CMUT2222A

ULTRAmi™ SURFACE MOUNT
NPN SILICON TRANSISTOR

ULTRAmi™



SOT-523 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUT2222A type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in an ULTRAmi™ surface mount package, designed for small signal general purpose and switching applications. Marking Code is PC1.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CB0}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I_{CBO}	$V_{CB}=60\text{V}$		10	nA
I_{CBO}	$V_{CB}=60\text{V}, T_A=125^\circ\text{C}$		10	μA
I_{EBO}	$V_{EB}=3.0\text{V}$		10	nA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$		10	nA
BV_{CB0}	$I_C=10\mu\text{A}$	75		V
BV_{CEO}	$I_C=10\text{mA}$	40		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	35		
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50		
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40		

ELECTRICAL CHARACTERISTICS: Continued

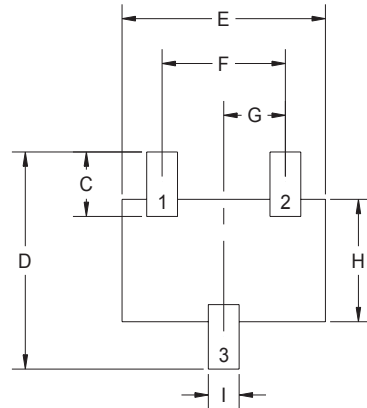
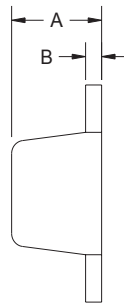
<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	300		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		25	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	2.0	8.0	k Ω
h_{ie}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	0.25	1.25	k Ω
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$		8.0	$\times 10^{-4}$
h_{re}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$		4.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	300	
h_{fe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	75	375	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	5.0	35	μ mhos
h_{oe}	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	25	200	μ mhos
$rb'C_C$	$V_{CB}=10V, I_E=20mA, f=31.8MHz$		150	ps
NF	$V_{CE}=10V, I_C=100\mu A, R_S=1.0k\Omega, f=1.0kHz$		4.0	dB
t_d	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		10	ns
t_r	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		25	ns
t_s	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225	ns
t_f	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		60	ns

MECHANICAL OUTLINE - SOT-523

BOTTOM VIEW

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.025	0.029	0.63	0.73
B	0.004	0.005	0.10	0.13
C	0.015	0.019	0.39	0.49
D	0.061	0.065	1.55	1.65
E	0.061	0.065	1.55	1.65
F	0.039	0.040	0.98	1.02
G	0.019	0.020	0.48	0.52
H	0.033	0.037	0.83	0.93
I	0.009	0.010	0.23	0.25

SOT-523 (REV: R1)



R1

LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

R1 (2 -October 2001)